

Data Sheet

Description

KGF65A3L, MGF65A3L, and FGF65A3L are 650 V Field Stop IGBTs. Sanken original trench structure decreases gate capacitance, and achieves low saturation voltage and switching losses reduction. Thus, Field Stop IGBTs can improve the efficiency of your circuit.

Features

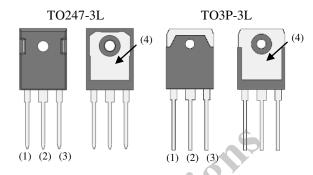
- Low Saturation Voltage
- High Speed Switching
- With Integrated Fast Recovery Diode
- Bare lead frame: Pb-free (RoHS compliant)

• V _{CE}	650 V
• $I_C (T_C = 100 ^{\circ}C)$	30 A
• Short Circuit Withstand Time -	5 μs
• V _{CE(sat)}	1.6 V typ.
• $t_f (T_J = 175 ^{\circ}C)$	
• V _F	1.6 V typ.

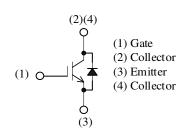
Applications

- Uninterruptible Power Supply (UPS)
- Inverter Circuit
- Bridge Circuit

Package







Selection Guide

cations	(1) (2) (3)	
nterruptible Power Supply (UPS) rter Circuit ge Circuit	(2)(4)	(1) Gate (2) Collector (3) Emitter (4) Collector
	Selection Guide	
	Part Number	Package
	KGF65A3L	TO247-3L
	MGF65A3L	TO3P-3L
>	FGF65A3L	TO3PF-3L

KGF65A3L, MGF65A3L, FGF65A3L

Absolute Maximum Ratings

Unless otherwise specified, $T_A = 25$ °C

Parameter	Symbol	Conditions	Rating	Unit	Remarks
Collector to Emitter Voltage	V_{CE}		650	V	
Gate to Emitter Voltage	V_{GE}		±30	V	
Continuous Collector Current (1)	$I_{\rm C}$	$T_C = 25 ^{\circ}C$	50	A	
		$T_{\rm C} = 100 {}^{\circ}{\rm C}$	30	A	
Pulsed Collector Current	I _{C(PULSE)}	PW ≤ 1 ms, duty cycle ≤ 1%	90	A	
Diode Continuous Forward Current (1)	I_{F}	$T_C = 25 ^{\circ}C$	40 ⁽²⁾	A	
		$T_{\rm C} = 100 {}^{\circ}{\rm C}$	30	A	S
Diode Pulsed Forward Current	I _{F(PULSE)}	$PW \le 1 \text{ ms},$ duty cycle $\le 1\%$	90	A	
Short Circuit Withstand Time	t_{SC}	$V_{GE} = 15 \text{ V},$ $V_{CE} = 400 \text{ V}$ $T_{J} = 175 ^{\circ}\text{C}$	5	μs	
Power Dissipation	P_{D}	T _C = 25 °C	217	W	MGF65A3L KGF65A3L FGF65A3L
Operating Junction Temperature	T_{J}	4	175	°C	
Storage Temperature Range	T_{STG}		−55 to 150	°C	
Isolation Voltage	V _{ISO(RMS)}	Between surface of case and all pins that are shorted; AC, 60 Hz, 1 min	1500	V	FGF65A3L

Thermal Characteristics

Unless otherwise specified, $T_A = 25$ °C

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	Remarks
Thermal Resistance of IGBT	R _{0JC} (IGBT)		_	_	0.69	°C/W	MGF65A3L KGF65A3L
(Junction to Case)			_		2.08		FGF65A3L
Thermal Resistance of Diode (Junction to Case)	R _{0JC} (Di)			1.15		MGF65A3L	
					1.13	°C/W	KGF65A3L
			_	_	2.28		FGF65A3L

 $^{^{(1)}}$ I_C and I_F are determined by the maximum junction temperature for TO3P-3L package. $^{(2)}$ Determined by bonding wires capability.

KGF65A3L, MGF65A3L, FGF65A3L

Electrical Characteristics

Unless otherwise specified, $T_A = 25$ °C

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit		
Collector to Emitter Breakdown Voltage	V _{(BR)CES}	$I_C = 100 \ \mu A, \ V_{GE} = 0 \ V$	650		_	V		
Collector to Emitter Leakage Current	I_{CES}	$V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$		_	100	μΑ		
Gate to Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 30 \text{ V}$	_		±500	nA		
Gate Threshold Voltage	V _{GE(TH)}	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$	4.0	5.5	7.0	V		
Collector to Emitter Saturation Voltage	V _{CE(sat)}	$V_{GE} = 15 \text{ V}, I_{C} = 30 \text{ A}$	_	1.6	1.96	V		
Input Capacitance	C_{ies}	$V_{CE} = 20 \text{ V},$	_	1800				
Output Capacitance	C_{oes}	$V_{GE} = 0 V$,	_	200	0 -	pF		
Reverse Transfer Capacitance	C _{res}	f = 1.0 MHz,	_	80				
Gate charge	Q_{g}	$V_{CE} = 520 \text{ V}, I_{C} = 30 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	60	_	nC		
Turn-on Delay Time	$t_{d(on)}$		4	30	_	ns		
Rise Time	t _r	<i>A</i>		30	_			
Turn-off Delay Time	$t_{d(off)}$	$T_I = 25 ^{\circ}\text{C},$	_	90	_			
Fall Time	t_{f}	see Figure 1.	_	40	_			
Turn-on Energy (3)	Eon			0.6				
Turn-off Energy	E _{off}			0.6		mJ		
Turn-on Delay Time	t _{d(on)}			30				
Rise Time	$t_{\rm r}$			30				
Turn-off Delay Time	t _{d(off)}	$T_{\rm J} = 175 {\rm ^{\circ}C},$		120		ns		
Fall Time	t_{f}	see Figure 1.		160				
Turn-on Energy (3)	Eon			1.1				
Turn-off Energy	E _{off}			1.1		mJ		
Emitter to Collector Diode Forward Voltage	V_{F}	$I_F = 30 \text{ A}$		1.6		V		
Emitter to Collector Diode Reverse Recovery Time	t _{rr}	$I_F = 30 \text{ A},$ $di/dt = 700 \text{ A/}\mu\text{s}$		50		ns		

 $^{\left(3\right) }$ Energy losses include the reverse recovery of diode.

Test Circuits and Waveforms

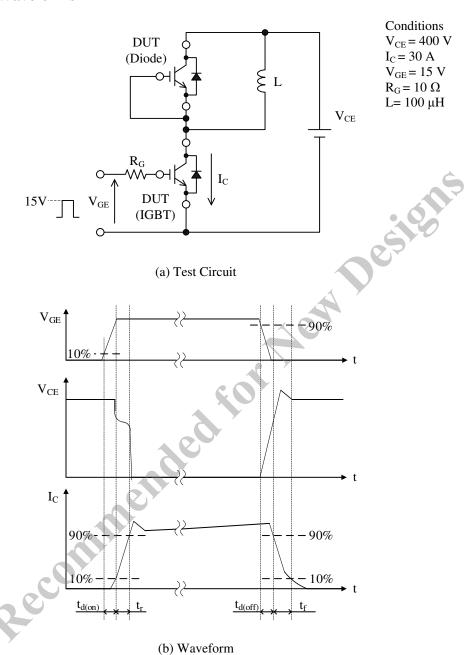


Figure 1. Test Circuits and Waveforms of dv/dt and Switching Time

Rating and Characteristic Curves

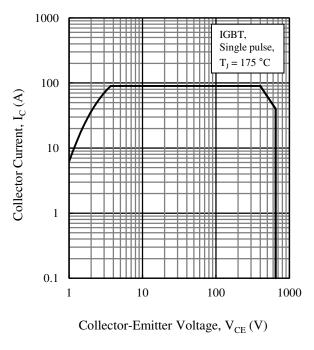


Figure 2. IGBT Reverse Bias Safe Operating Area

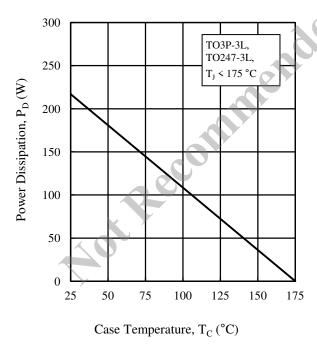


Figure 4. Power Dissipation vs. Case Temperature

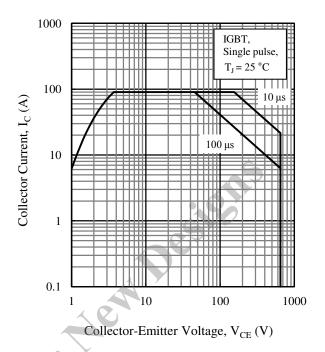


Figure 3. IGBT Safe Operating Area

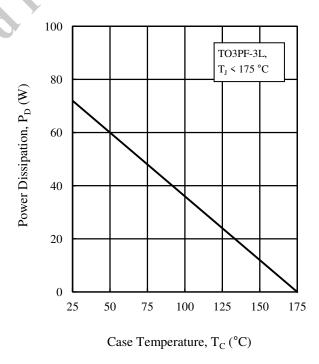


Figure 5. Power Dissipation vs. Case Temperature

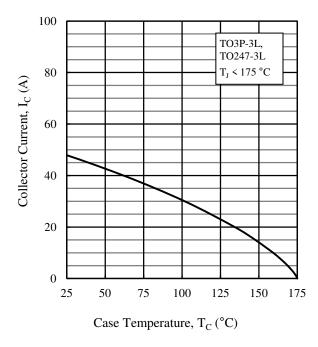


Figure 6. Collector Current vs. Case Temperature

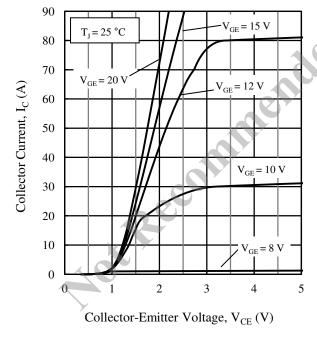


Figure 8. Output Characteristics ($T_J = 25$ °C)

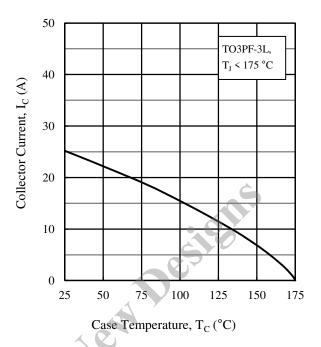


Figure 7. Collector Current vs. Case Temperature

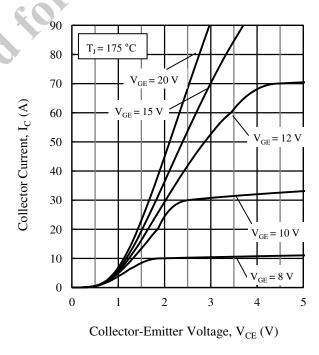


Figure 9. Output Characteristics ($T_J = 175$ °C)

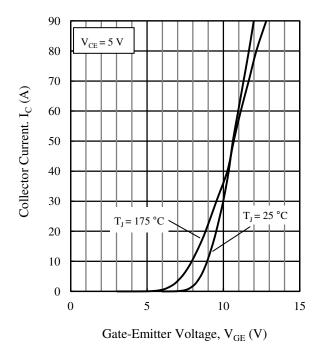


Figure 10. Transfer Characteristics

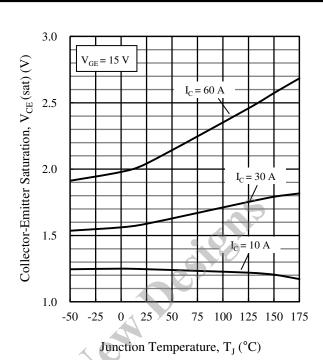


Figure 11. Saturation Voltage vs. Junction Temperature

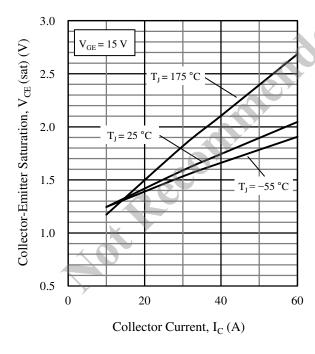


Figure 12. Saturation Voltage vs. Collector Current

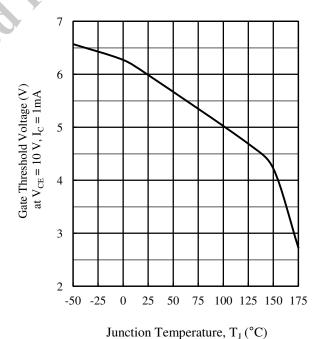


Figure 13. Gate Threshold Voltage vs. Junction Temperature

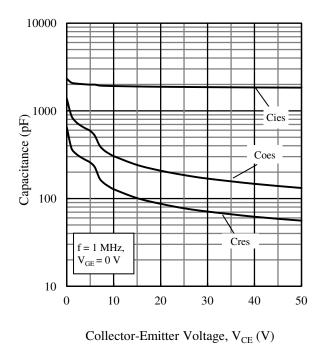


Figure 14. Capacitance Characteristics

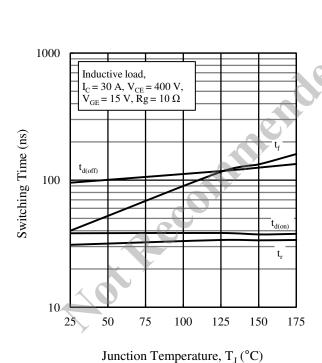


Figure 16. Switching Time vs. Junction Temperature

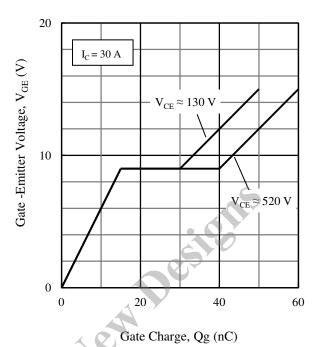


Figure 15. Typical Gate Charge

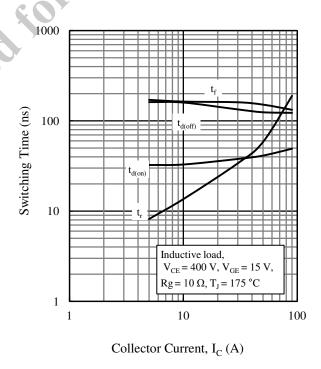


Figure 17. Switching Time vs. Collector Current

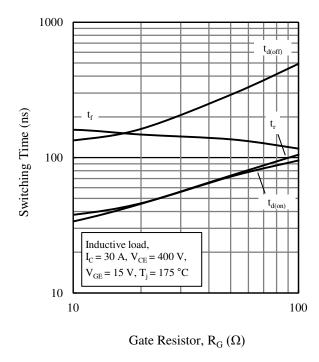


Figure 18. Switching Time vs. Gate Resistor

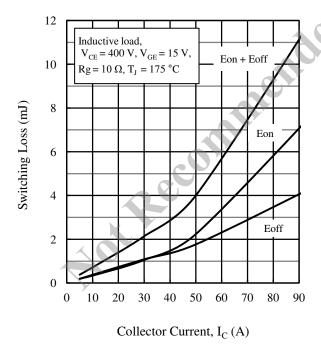


Figure 20. Switching Loss vs. Collector Current

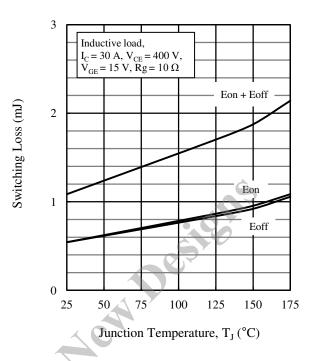


Figure 19. Switching Loss vs. Junction Temperature

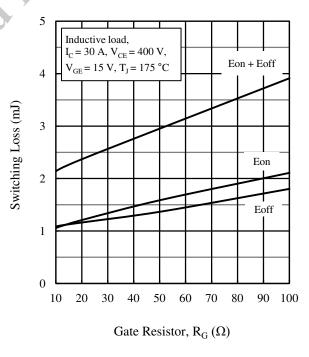


Figure 21. Switching Loss vs. Gate Resistor

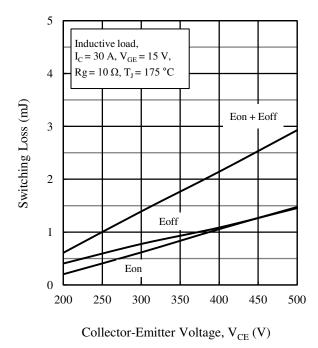


Figure 22. Switching Loss vs. Collector-Emitter Voltage

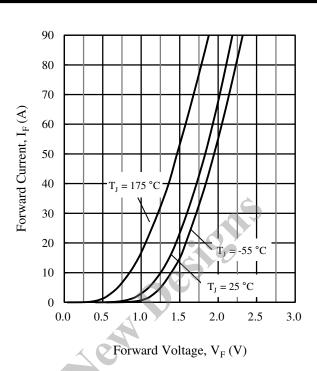


Figure 23. Diode Forward Characteristics

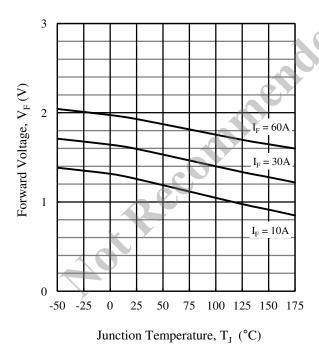


Figure 24. Diode Forward Voltage vs. Junction Temperature

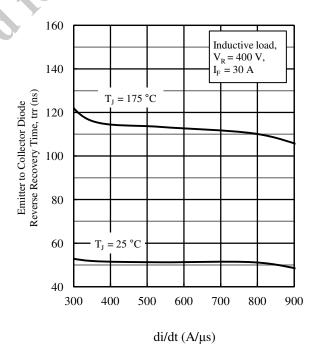


Figure 25. Emitter to Collector Diode Reverse Recovery Time vs. di/dt

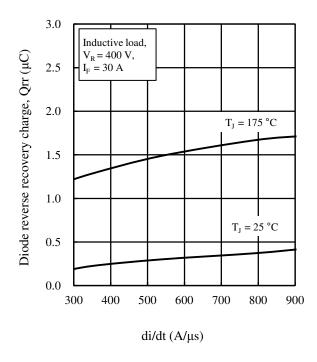


Figure 26. Diode Reverse Recovery Charge vs. di/dt

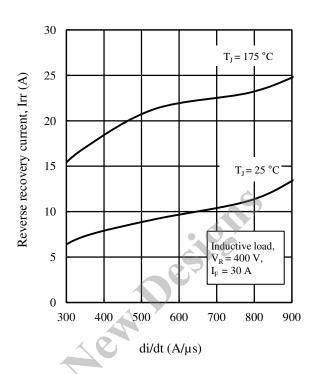


Figure 27. Recovery Current vs. di/dt

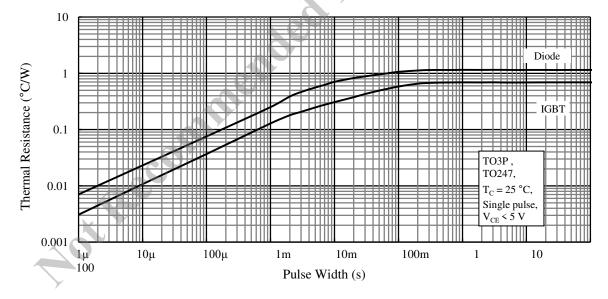
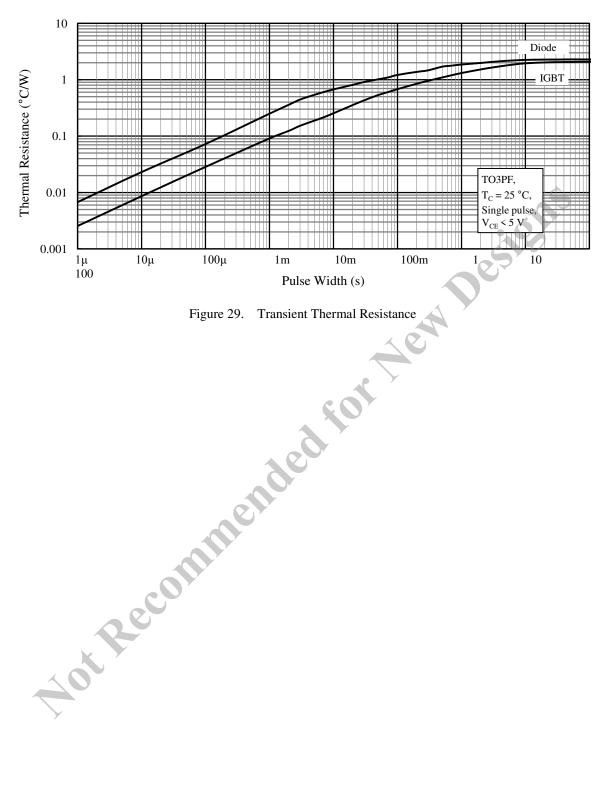
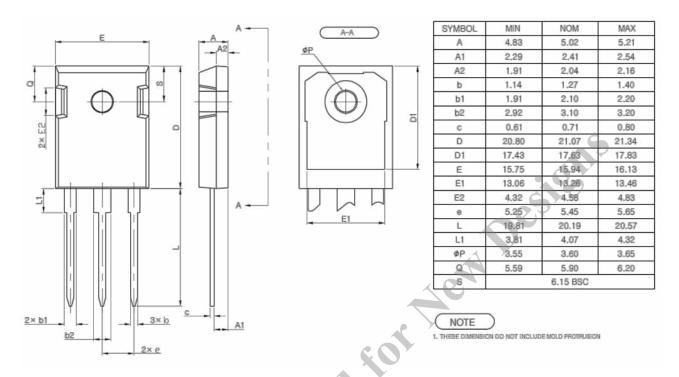


Figure 28. Transient Thermal Resistance

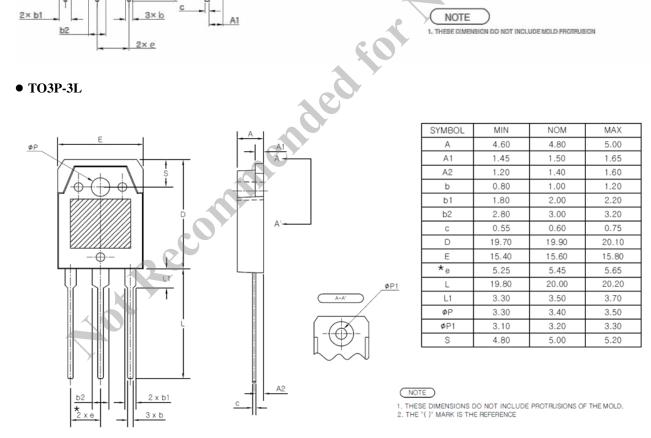


Physical Dimensions

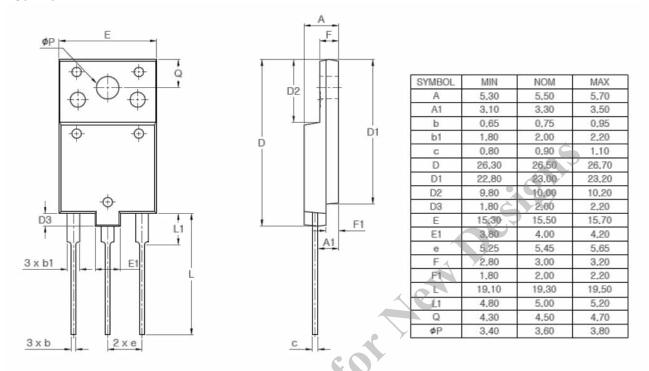
• TO247-3L



• TO3P-3L



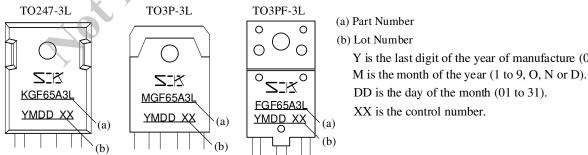
• TO3PF-3L



NOTES:

- Dimensions in millimeters
- Bare lead frame for TO247, TO3P and TO3PF: Pb-free (RoHS compliant)
- When soldering the products, make sure to minimize the working time within the following limits: Flow: 260 ± 5 °C / 10 ± 1 s, 2 times
 - Soldering Iron: 380 ± 10 °C / 3.5 ± 0.5 s, 1 time (Soldering should be at a distance of at least 1.5 mm from the body of the products.)
- Soldering should be at a distance of at least 1.5 mm from the body of the products.
- The recommended screw torque for TO247 and TO3P: 0.686 to 0.882 N·m (7 to 9 kgf·cm)

Marking Diagram



Y is the last digit of the year of manufacture (0 to 9).

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